YJ Planar Fast Recovery Diode Die Specification

600V 8A, Fast recovery diode die based on silicon planar process
Part No.: FRD08A600AS-290A

Main Products Characterstics

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	600V
Average forward current		8A
(tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	80A
Storage temperature range	T_{stg}	-40 to +150 °C
Maximum operating junction temperature	T_j	150 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
Reverse breakdown voltage I_R = 50uA		630V	680V
I_F ≤ 2%		1.6V	
Reverse Recovery Time I_F=0.5A, I_R=1A, I_{rr}=0.25A	Trr		28ns
Maximum reverse current V_R = V_{RRM} ≤ 2%		2uA	

Device Schematics and Outline Drawing

Die Thickness
Die Size *
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 *: Cutting street width is around 40um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

0514-80982389
0514-80980189